

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Withdrawn) An apparatus for manufacturing a semiconductor device, comprising:

a first chamber having a first substrate holder provided in the lower portion of the first chamber for mounting a sample thereon, a halogen lamp provided in the upper portion of the first chamber for irradiating lamp light to the sample, and a substrate door through which the sample passes;

a second chamber having a temperature-adjustable second substrate holder provided in the lower portion of the second chamber for mounting the sample thereon, a middle film provided in the middle portion of the second chamber for dividing the chamber into an upper portion and a lower portion, an elevating portion attached to said second substrate holder for moving said second substrate holder into the upper portion or the lower portion on the basis of the middle film, and a metal depositing portion provided in the upper portion of the second chamber;

pumping portions connected to said first chamber and said second chamber, for adjusting the pressures thereof, respectively;

gas injecting portions connected to said first chamber and said second chamber, for injecting a gas by a certain amount, respectively; and

a connecting portion for allowing the sample to reciprocally moving between said first chamber and said second chamber without injecting outside air, and

the connecting portion including a gate valve.
2. (Withdrawn) The apparatus for manufacturing the semiconductor device according to claim 1, wherein said metal depositing portion includes a sputtering gun, a sputter shutter for preventing the metal to be deposited from being spread into the both side thereof during the sputtering process, and a shutter stop for adjusting the aperture of the sputter shutter.

3. (Withdrawn) The apparatus for manufacturing the semiconductor device according to claim 1, wherein said pumping portion uses a rotary pump and a turbo molecular pump.
4. (Withdrawn) The apparatus for manufacturing the semiconductor device according to claim 1, further comprising thermocouples attached to said first substrate holder and said second substrate holder for measuring the temperatures of said first chamber and said second chamber, respectively.
5. (Withdrawn) The apparatus for manufacturing the semiconductor device according to claim 1, further comprising a port provided on the side surface of said first chamber for providing an UV lamp or an electronic source.
6. **(Currently Amended)** A method for manufacturing a semiconductor device, ~~using the apparatus for manufacturing the semiconductor device according to claim 1~~ comprising the steps of:
- cleaning a substrate on which a semiconductor structure is formed, ~~by using said in a~~ first chamber, said first chamber having a substrate holder provided in a lower portion thereof, a halogen lamp provided in an upper portion of the first chamber and a substrate door through which the substrate is allowed to pass;
- moving said substrate into ~~said a~~ second chamber after cleaning the substrate, said second chamber having a temperature-adjustable second substrate holder provided in a lower portion of the second chamber, said holder configured to receive the substrate from the first chamber thereon, a middle film provided in a middle portion of the second chamber, said middle film dividing the second chamber into an upper portion and a lower portion, an elevating portion attached to said second substrate holder for moving said second substrate holder between the upper portion and the lower portion, and a metal depositing portion provided in the upper portion of the second chamber; and
- depositing a metal film by said metal depositing portion by sputtering, wherein a sputter shutter prevents the metal to be deposited from being spread on sides thereof; wherein

a connecting portion connects said first chamber and said second chamber for allows the substrate to move between said first chamber and said second chamber, wherein

said connecting portion being sealed thereby preventing a passage of outside air therein; and wherein

the steps of cleaning moving and depositing are performed in batch process, without being exposed to outside air.

7. (Original) The method for manufacturing the semiconductor device according to claim 6, further comprising heating the substrate after depositing the metal film.

8. (Original) The method for manufacturing the semiconductor device according to claim 6, further comprising growing a sacrificial oxide film in said second chamber, before depositing the metal film.

9. **(Currently Amended)** A method for manufacturing a Schottky ~~schottky~~-barrier MOSFET ~~using the apparatus for manufacturing the semiconductor device according to claim 1,~~ comprising the steps of:

positioning a substrate on which a silicon layer, a gate oxide layer, a gate electrode, a spacer is formed in sequence, ~~in said~~ in a first chamber, said first chamber having a substrate holder provided in a lower portion thereof, a halogen lamp provided in an upper portion of the first chamber and a substrate door through which the substrate is allowed to pass;

cleaning the substrate by using said first chamber, before depositing a metal film for forming a source/drain electrode;

moving said substrate ~~into said~~ into a second chamber through said connecting a connecting portion connecting said second chamber and the first chamber, after cleaning the substrate, said second chamber having a temperature-adjustable second substrate holder provided in a lower portion of the second chamber configured to receive the substrate from the first chamber thereon, a middle film provided in a middle portion of the second chamber, said middle film dividing the second chamber into an upper portion and a lower portion, an elevating portion attached to said second substrate holder for moving said second substrate holder between the

upper portion and the lower portion, and a metal depositing portion provided in the upper portion of the second chamber;

and ~~pulling up~~ moving the substrate in an upward direction into the ~~to the~~ upper portion of the second chamber;

depositing a metal film by using said metal depositing portion by sputtering, wherein a sputter shutter prevents the metal to be deposited from being spread on sides thereof; and

~~pulling down~~ moving the substrate in a downward direction and heating the substrate to form a silicide, after depositing the metal film.

10. **(Currently Amended)** The method for manufacturing the ~~schottky~~ Schottky barrier MOSFET according to claim 9, further comprising growing a sacrificial oxide film in said second chamber, before depositing said metal film.

11. **(Currently Amended)** The method for manufacturing the ~~Schottky~~ Schottky barrier MOSFET according to claim 9, wherein ~~said the said~~ step of cleaning is performed by a vacuum cleaning process or a H₂ baking process, said vacuum cleaning process is performed by heating the substrate ~~to the~~ to a temperature of 650-750° C during 60-300 seconds, under ~~the ultraan ultra~~ high vacuum state in which the pressure is equal to and less than 10⁻⁸ Torr, and said H₂ baking process is performed by heating the substrate to the temperature of 700-900°C during 60-300 seconds under the condition that H₂ gas flows in the extent of 0.5-50 slm and pressure is maintained at 0.1-10 Torr.

12. **(Currently Amended)** The method for manufacturing the ~~Schottky~~ Schottky barrier MOSFET according to claim 10, wherein the step of growing the sacrificial oxide film is performed in the lower portion of said second chamber, and includes the step of maintaining the substrate at the pressure equal to and less than 10^{sup.-8} Torr and the temperature of 550-750°C during 100-500 seconds and injecting Si₂H₆ or SiH₄ gas into the chamber by 1-50 seem to form a selective silicon layer.

13. **(Currently Amended)** The method for manufacturing the Schottky ~~schottky~~-barrier MOSFET according to claim 9, wherein the step of depositing the metal film is performed by using a sputtering method under the state of the pressure of 0.005-50 Torr ~~and the~~ and an atmosphere of Ar or N₂ gas, ~~and the~~ and a thickness of the deposited metal film is in the range of 50-500 Å°.

14. **(Currently Amended)** The method for manufacturing the Schottky ~~schottky~~-barrier MOSFET according to claim 9, wherein the step of heating the substrate for forming the silicide is performed in said first chamber at the pressure equal to and less than 10⁻⁸ Torr.